

## Features

- Ultra Bright
- High Performance
  - 5.5mW (460nm) Deep Blue
  - 5.0mW (470nm) Blue
  - 4.8mW (490nm) Aqua Blue
  - 3.5mW (505nm) Traffic Green
  - 3.0mW (525nm) Green
- Single Wire Bond Structure

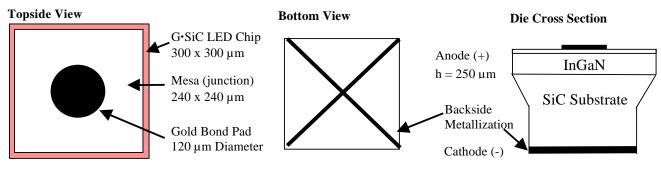
- Applications
- Outdoor LED Video Displays
- Automotive Dashboard Lighting
- White LEDs
- Backlighting
- Traffic Signals

Class II ESD Rating

# Description

Cree's UB series of ultra bright LEDs are a new generation of solid state LED emitters which combine highly efficient InGaN materials with Cree's proprietary SiC substrate to deliver superior price performance for high intensity blue and green LEDs. These LED chips have a geometrically enhanced vertical chip structure to maximize light extraction efficiency, and require only a single wire bond connection. Cree's UB series chips are individually tested for conformity to optical and electrical specifications and the ability to withstand 1000V ESD. These LEDs are useful in a broad range of applications such as outdoor full motion LED video signs, automotive lighting and white LEDs, yet can also be used in high volume applications such as LCD backlighting. Cree's UB series chips are compatible with most radial and SMT LED assembly processes.

# CXXX-UB290-E1000 Chip Diagram



## G•SiC<sup>®</sup> Technology Ultra Bright LEDs CXXX-UB290-E1000

# *Maximum Ratings at* $T_A = 25 \circ C^{\text{Notes } 1\&3}$

	CXXX-UB290-E1000
DC Forward Current	30mA
Peak Forward Current (1/10 duty cycle @ 1kHz)	100mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature Range	$-20^{\circ}$ C to $+80^{\circ}$ C
Storage Temperature Range	-30°C to +100°C
Electrostatic Discharge Threshold (HBM) Note 2	1000 V
Electrostatic Discharge Classification (MIL-STD-883E) Note 2	Class 2

Typical	Typical Electrical/Optical Characteristics at $T_A = 25^{\circ}C$ , If = 20mA <sup>Note 3</sup>									
Part Number	Vo	ward ltage <sub>f</sub> , V)		nt Flux mW)	Reverse Current [I(Vr=5V), μA]	Flux (mlm)	Peak Wavelength $(\lambda_{p}, nm)$	Dominant Wavelength $(\lambda_d, nm)$	Halfwidth $(\lambda_{D,} nm)$	Optical Rise Time (τ, ns)
	Тур	Max	Min	Тур	Max	Тур	Тур	Min Typ Max	Тур	Тур
C460	3.5	3.9	3.8	5.5	10	330	458	455 460 465	26	30
C470	3.5	3.9	3.4	5.0	10	440	468	465 470 475	26	30
C490	3.5	3.9	3.3	4.8	10	1000	488	485 490 495	26	30
C505	3.5	3.9	2.5	3.5	10	1140	502	500 505 510	30	30
C525	3.5	3.9	1.7	3.0	10	1400	518	520 525 535	35	30

#### Mechanical Specifications Note 4

	CXXX-UB290-E1000	
Description	Dimension	Tolerance
P-N Junction Area (µm)	240 x 240	± 25
Top Area (µm)	300 x 300	± 50
Bottom Area (µm)	200 x 200	± 25
Chip Thickness (µm)	250	± 25
Au Bond Pad Diameter (µm)	120	$\pm 20$
Au Bond Pad Thickness (µm)	1.2	$\pm 0.5$
Back Contact Metal Width (µm)	15	-5, +10

#### Notes:

1) Maximum ratings are package dependent. The above ratings were determined using a T-1 3/4 package (with Hysol OS4000 epoxy) for characterization. Seller makes no representations regarding ratings for packages other than the T-1 3/4 package used by Seller. The forward currents (DC and Peak) are not limited by the G •SiC die but by the effect of the LED junction temperature on the package. The junction temperature limit of 125°C is a limit of the T-1 3/4 package; junction temperature should be characterized in a specific package to determine limitations. Assembly processing temperature must not exceed 350°C (< 15 minutes).</p>

2) Product resistance to electrostatic discharge (ESD) is measured by simulating ESD using a rapid avalanche energy test (RAET). The RAET procedures are designed to approximate the maximum ESD ratings shown. Seller gives no other assurances regarding the ability of Products to withstand ESD.

3) All Products conform to the listed minimum and maximum specifications for electrical and optical characteristics, when assembled and operated at 20 mA within the maximum ratings shown above. Efficiency decreases at higher currents. Typical values given are the average values expected by Seller in large quantities and are provided for information only. Seller gives no assurances Products shipped will exhibit such typical ratings. All measurements were made using lamps in T-1 3/4 packages (with Hysol OS4000 epoxy). Optical characteristics were measured in a Photoresearch Spectrascan Integrating Sphere. Illuminance E.

4) All Products conform to the listed mechanical specifications within the tolerances shown.

5) Caution: To obtain optimum output efficiency, the maximum height of die attach epoxy on the side of the chip should not exceed 80µm.